

BUK7Y18-75B

N-channel TrenchMOS standard level FET

1 March 2013

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters
- Engine management
- General purpose power switching
- Motors, lamps and solenoids
- Transmission control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	75	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> ; <u>Fig. 4</u>		-	-	49	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	105	W
Static charact	eristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 12; Fig. 13		-	13.8	18	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 20 A; V _{DS} = 60 V; V _{GS} = 10 V; Fig. 14		-	14.24	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)} S	non-repetitive drain- source avalanche energy	I_D = 49 A; $V_{sup} \le 75$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	118	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D 1
2	S	source		
3	S	source	[d]	G-VIII
4	G	gate	<u> </u>	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Table 5. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7Y18-75B	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y18-75B	71875B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	75	V
V_{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	75	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> ; <u>Fig. 4</u>	-	49	Α
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	34.9	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	198	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	105	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drai	in diode				'	,
I _S	source current	T _{mb} = 25 °C		-	49	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	198	Α
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 49 A; V_{sup} ≤ 75 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	118	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 3	[1][2][3]	-	-	J

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Repetitive avalanche rating limited by an average junction temperature of 170 °C.
- [3] Refer to application note AN10273 for further information.

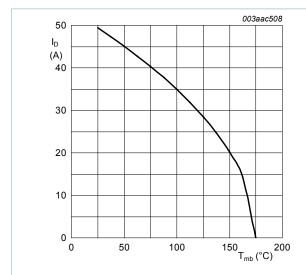


Fig. 1. Continuous drain current as a function of mounting base temperature

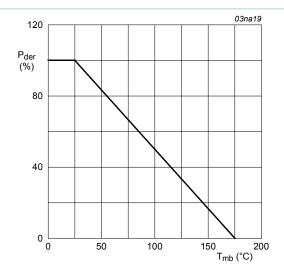
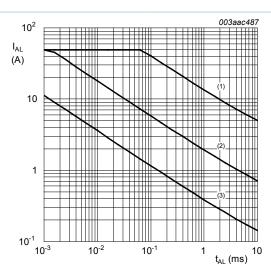


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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- (1) Single pulse; $T_j = 25$ °C.
- (2) Single pulse; $T_i = 150$ °C.
- (3) Repetitive.

Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

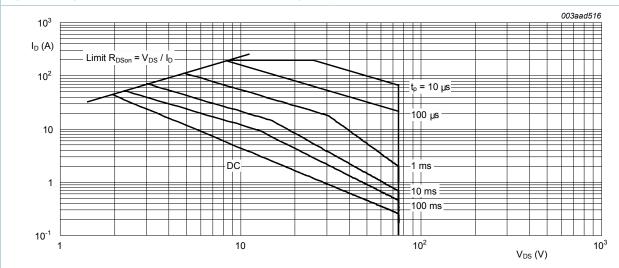


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

$$T_{mb} = 25 \,^{\circ}C; I_{DM}$$
 is single pulse

9. Thermal characteristics

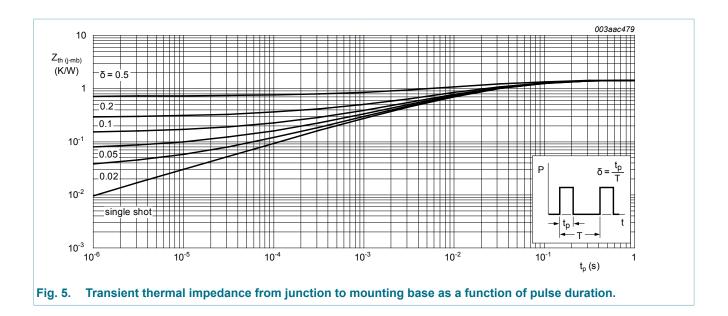
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.42	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	75	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	68	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 75 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 75 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 20 A; T _j = 175 °C; Fig. 12; Fig. 13	-	-	43.2	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 12; Fig. 13	-	13.8	18	mΩ
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 60 V; V _{GS} = 10 V;	-	35	-	nC
Q _{GS}	gate-source charge	Fig. 14	-	8.28	-	nC
Q _{GD}	gate-drain charge	1	-	14.24	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	1630	2173	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	274	329	pF
C _{rss}	reverse transfer capacitance			-	115	158	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_{L} = 1.5 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω		-	18.5	-	ns
t _r	rise time			-	22.5	-	ns
t _{d(off)}	turn-off delay time			-	44.5	-	ns
t _f	fall time			-	19.8	-	ns
Source-dra	ain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 25 V; T_j = 25 °C; Fig. 16		-	0.85	1.2	V
t _{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 30 V		-	55.4	-	ns
Q _r	recovered charge			-	143	-	nC

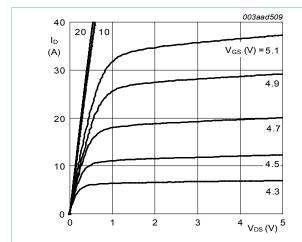


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values.



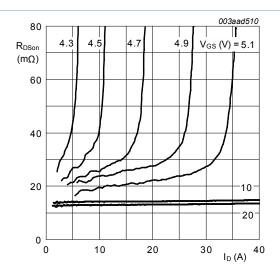


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values.

$$T_j = 25\,^{\circ}C$$

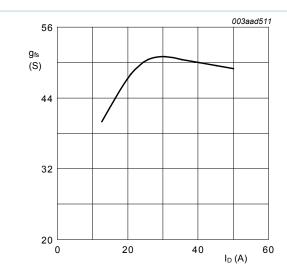


Fig. 8. Forward transconductance as a function of drain current; typical values.

$$T_j = 25 \,^{\circ}C; V_{DS} = 25 \,^{\circ}V$$

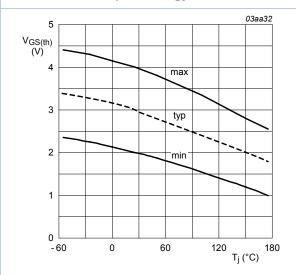


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = \mathbf{1} m A; V_{DS} = V_{GS}$$

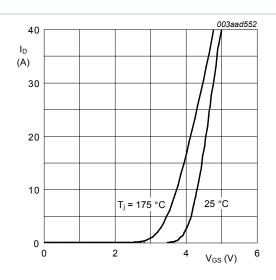


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

$$V_{\rm DS}=25\,V$$

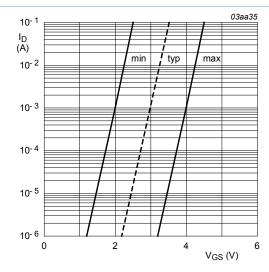


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

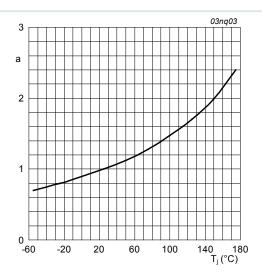


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

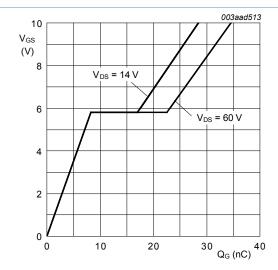


Fig. 14. Gate-source voltage as a function of gate charge; typical values.

$$T_j = 25 \,^{\circ}C; I_D = 20A$$

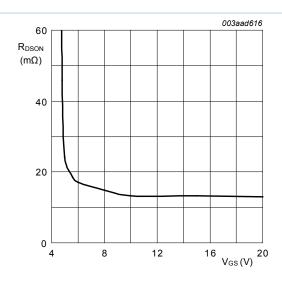


Fig. 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.

$$T_j=25\,^{\circ}C; I_D=20A$$

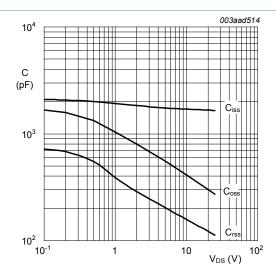


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

$$V_{GS} = 0V; f = 1MHz$$

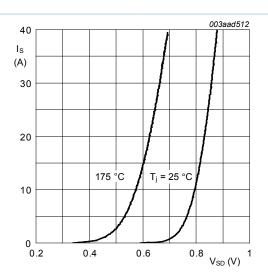
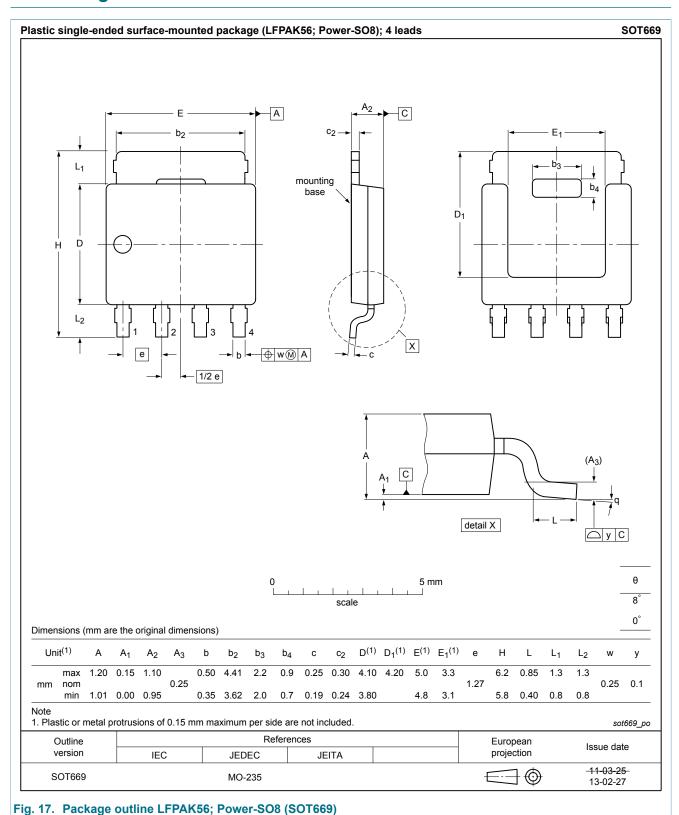


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

$$V_{\rm GS} = 0 \, V$$

11. Package outline



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12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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